

# REMARKS/ARGUMENT

The applicants' attorneys appreciate the Examiner's search and comments.

Claims 1 and 3-13 are pending in the application.

Claim 1 has been rejected under 35 U.S.C. §103(a) over Williams, U.S. Patent No. 5,248,627 in view of Kalnitsky, U.S. Patent No. 5,418,174. Reconsideration is requested.

Claim 1 calls for, in combination with other limitations, "a gate electrode comprised of P-type polysilicon." It has been set forth that Williams teaches "a gate electrode (60)" comprised of P-type silicon. See Office Action, page 3, line 5. It is respectfully submitted that the latter conclusion is erroneous. Williams teaches that the "polysilicon film 60 is heavily doped with a suitable n-type dopant such as phosphorous". Col. 4, lines 42-43.

Furthermore, claim 1 requires the gate oxide layer to be less than 1000Å thick. It has been set forth that Williams teaches a p-type polysilicon gate electrode at col. 2, lines 51-60. See Office Action, at page 3, line 6. It is respectfully submitted that at col. 2, lines 60-68 Williams in fact teaches away from the use of a p-type polysilicon gate electrode that includes boron dopants in combination with a thin gate oxide in the order of less than 1000Å thick. Specifically, Williams states that the use of boron in the p-type polysilicon gate is unsatisfactory because it tends to diffuse out and "counter dope" the channel. Col. 2, lines 60-64. Reconsideration is requested.

Claims 3-13 depend from claim 1, and, therefore, include at least its limitations. These claims include other limitations, which in combination with those of claim 1, are not shown or suggested by the art of record.

The application is believed to be in condition for allowance. Such action is earnestly solicited.

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Asst. Commissioner for Patents, Washington, D.C. 20231, on August 8, 2002:

Respectfully submitted,

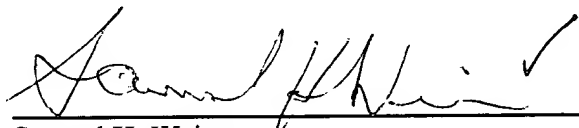
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Signature

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